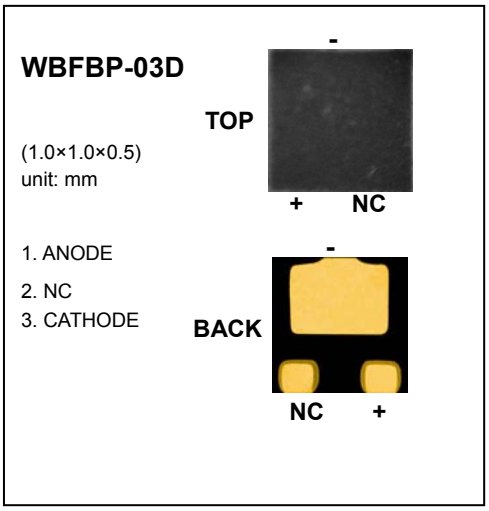
JIANGSU CHANGJIANG ELECTRONICS TECHNOLOGY CO., LTD

WBFBP-03D Plastic-Encapsulate DIODE



DK4448LLD03 SWITCHING DIODE

DESCRIPTION

Epitaxial planar Silicon diode

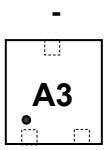
FEATURES

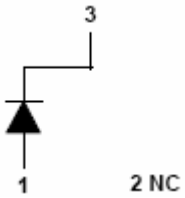
Fast Switching Speed
Ultra-Small Surface Mount Package
For General Purpose Switching Applications
High Conductance
Lead Free Product

APPLICATION

High Conductance Ultra Fast Diode
For portable equipment:(i.e. Mobile phone,MP3, MD,CD-ROM, DVD-ROM, Note book PC, etc.)

MARKING: **A3**





Maximum Ratings and Electrical Characteristics, Single Diode @T_A=25

Parameter	Symbol	Limits	Unit
Non-Repetitive Peak reverse voltage	V_{RM}	100	V
Peak Repetitive Peak reverse voltage **Working Peak Reverse Voltage** **DC Blocking Voltage**	V_{RRM} V_{RWM} V_R	80	V
RMS Reverse Voltage	$V_{R(RMS)}$	57	V
Forward Continuous Current	I_{FM}	500	mA
Average Rectified Output Current	I_O	250	mA
Peak forward surge current @=1.0μs **@=1.0s**	I_{FSM}	4.0 2.0	A
Power Dissipation	P_D	100	mW
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	1250	℃/W
Storage temperature	T_{STG}	-65 to +150	℃

Electrical Ratings @T_A=25℃

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Reverse Breakdown Voltage	V_R	80			V	I_R=2.5μA
Forward voltage	V_{F1}	0.62		0.72	V	I_F=5mA
	V_{F2}			0.855	V	I_F=10mA
	V_{F3}			1.0	V	I_F=100mA
	V_{F4}			1.25	V	I_F=150mA
Reverse current	I_{R1}			0.1	μA	V_R=70V
	I_{R2}			25	nA	V_R=20V
Capacitance between terminals	C_T			3.5	pF	V_R=6V,f=1MHz
Reverse Recovery Time	t_{rr}			4	ns	V_R=6V,I_F=5mA

Typical Characteristics DK4448LLD03

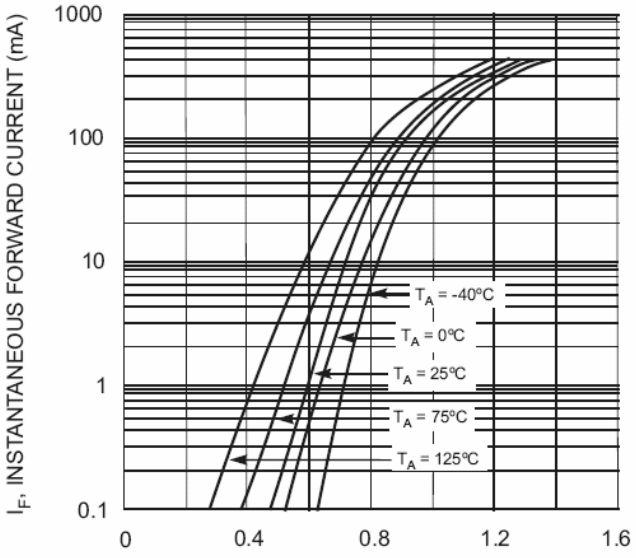


Fig. 1 Typical Forward Characteristics

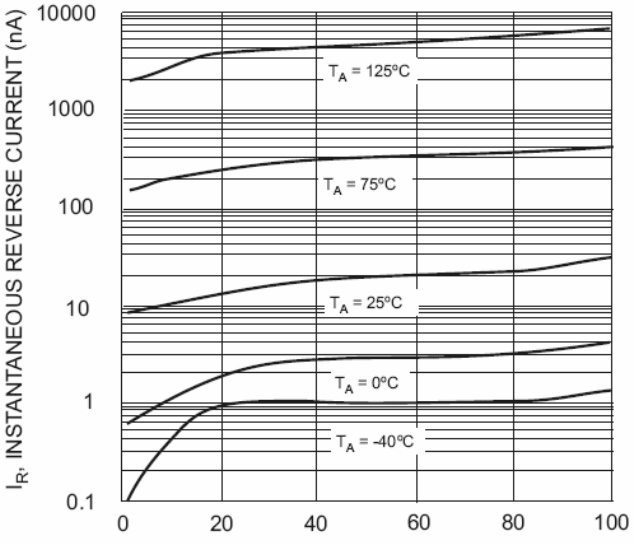


Fig. 2 Typical Reverse Characteristics

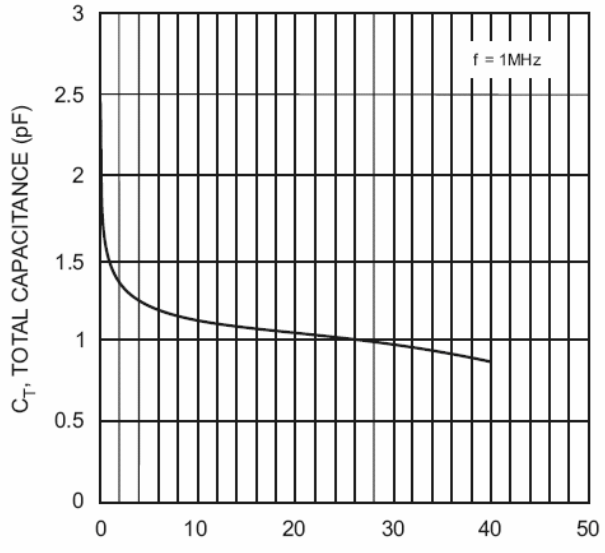


Fig. 3 Typical Capacitance vs. Reverse Voltage

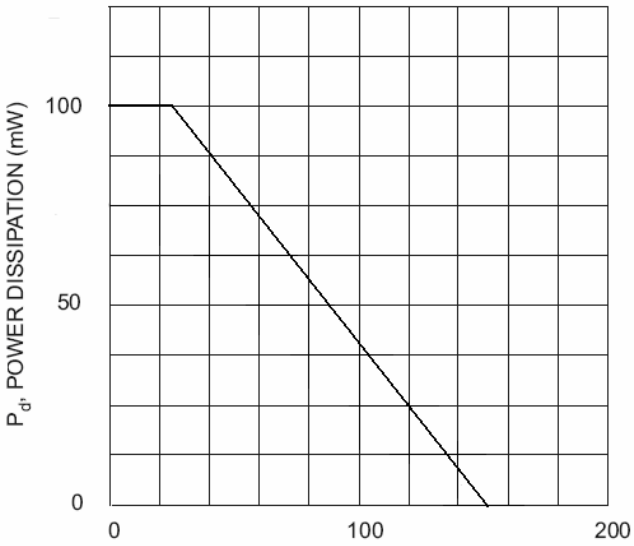


Fig. 4 Power Derating Curve, Total Package